

Features

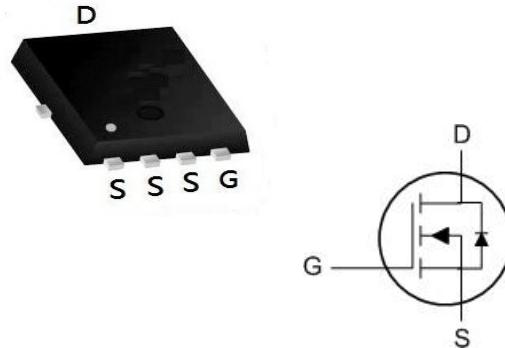
- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

BVDSS	RDS(on)	ID
60V	10mΩ	50A

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

PDFN5060-8L Pin Configuration**Absolute Maximum Ratings** ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	50	A
		$T_C = 100^\circ\text{C}$	29	A
I_{DM}	Pulsed Drain Current ^{note1}		180	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		36	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	60	W
$R_{θJC}$	Thermal Resistance, Junction to Case		2.5	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.0	1.6	2.5	V
$R_{DS(\text{on})}$ note3	Static Drain-Source on-Resistance	$V_{GS}=10\text{V}$, $I_D=20\text{A}$	-	10	13	mΩ
		$V_{GS}=4.5\text{V}$, $I_D=10\text{A}$	-	13	18	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	930	-	pF
C_{oss}	Output Capacitance		-	230	-	pF
C_{rss}	Reverse Transfer Capacitance		-	8	-	pF
Q_g	Total Gate Charge	$V_{DS}=30\text{V}$, $I_D=20\text{A}$, $V_{GS}=10\text{V}$	-	22	-	nC
Q_{gs}	Gate-Source Charge		-	4.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30\text{V}$, $I_D=20\text{A}$, $R_G=1.6\Omega$, $V_{GS}=10\text{V}$	-	4.5	-	ns
t_r	Turn-on Rise Time		-	2.7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	13.8	-	ns
t_f	Turn-off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	45	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	180	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_S=30\text{A}$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$T_J=25^\circ\text{C}$, $I_F=20\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$	-	18	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	12	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=12\text{A}$ 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

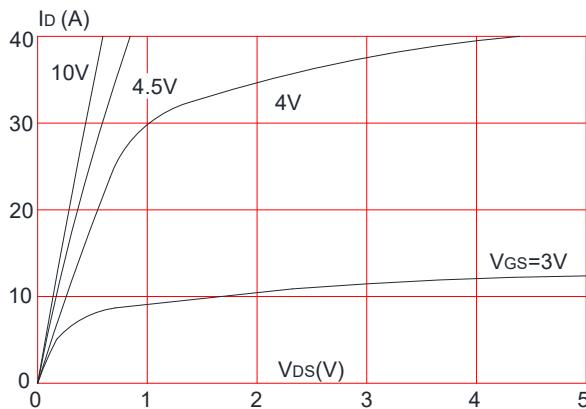


Figure 3: On-resistance vs. Drain Current

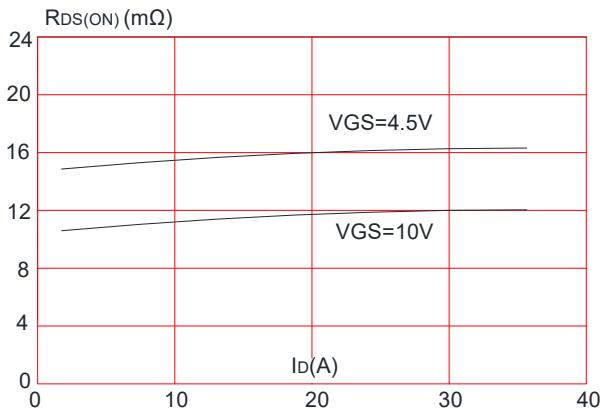


Figure 5: Gate Charge Characteristics

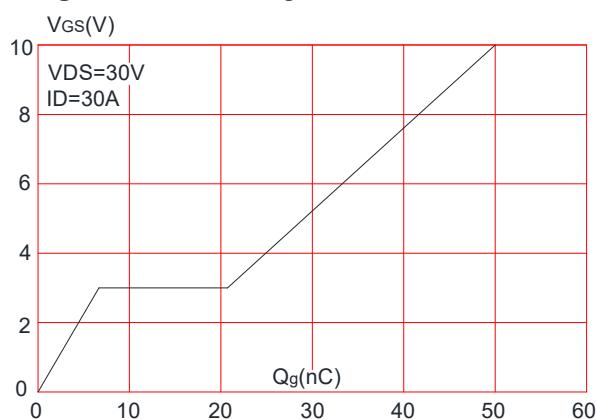


Figure 2: Typical Transfer Characteristics

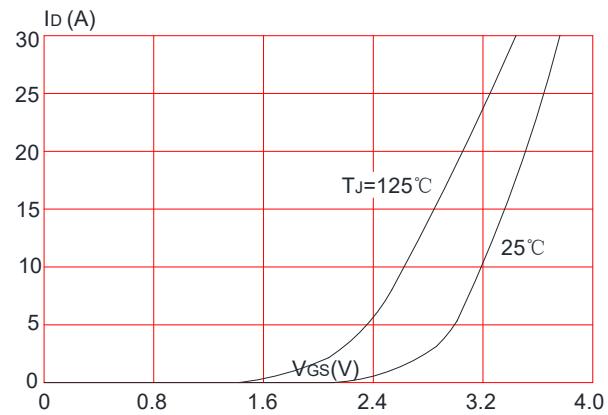


Figure 4: Body Diode Characteristics

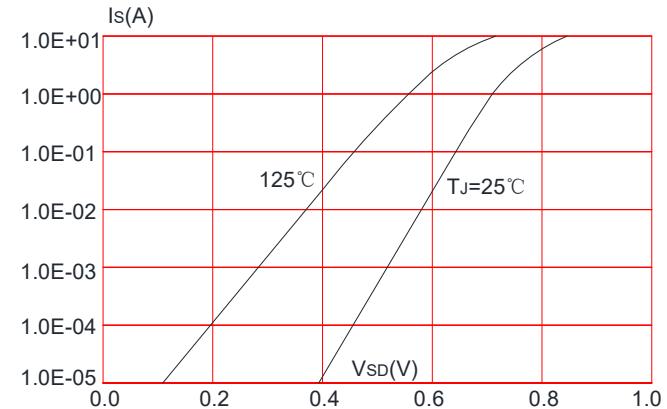


Figure 6: Capacitance Characteristics

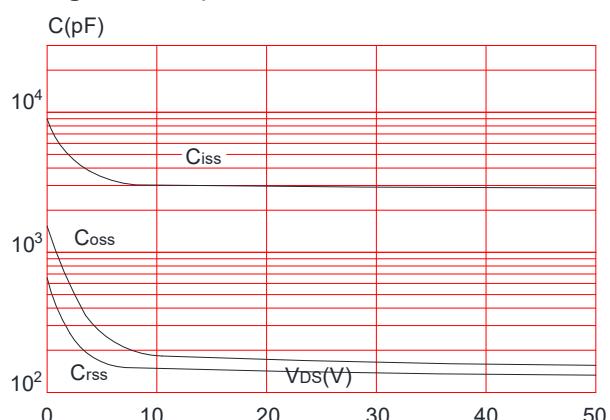


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

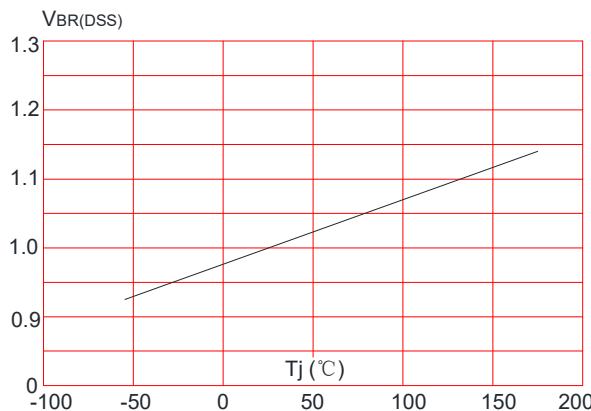


Figure 9: Maximum Safe Operating Area

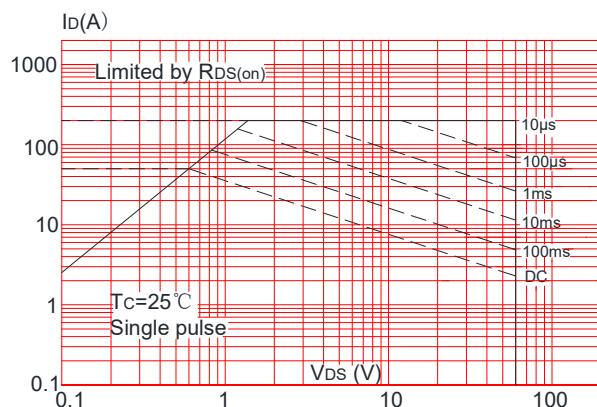


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

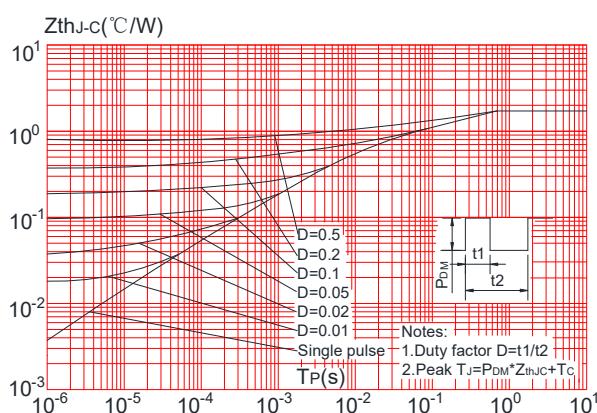


Figure 8: Normalized on Resistance vs. Junction Temperature

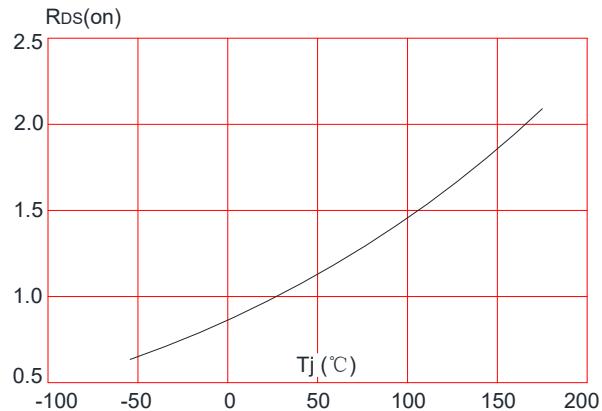
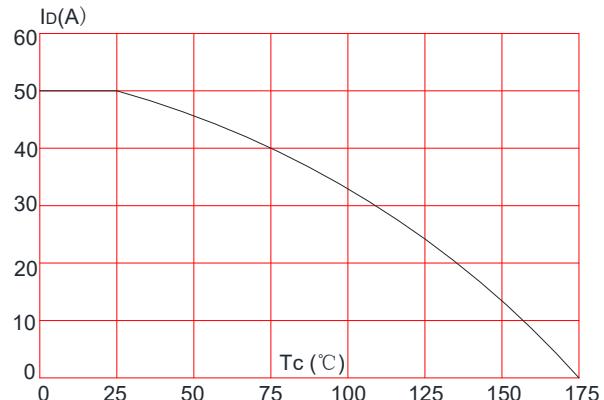
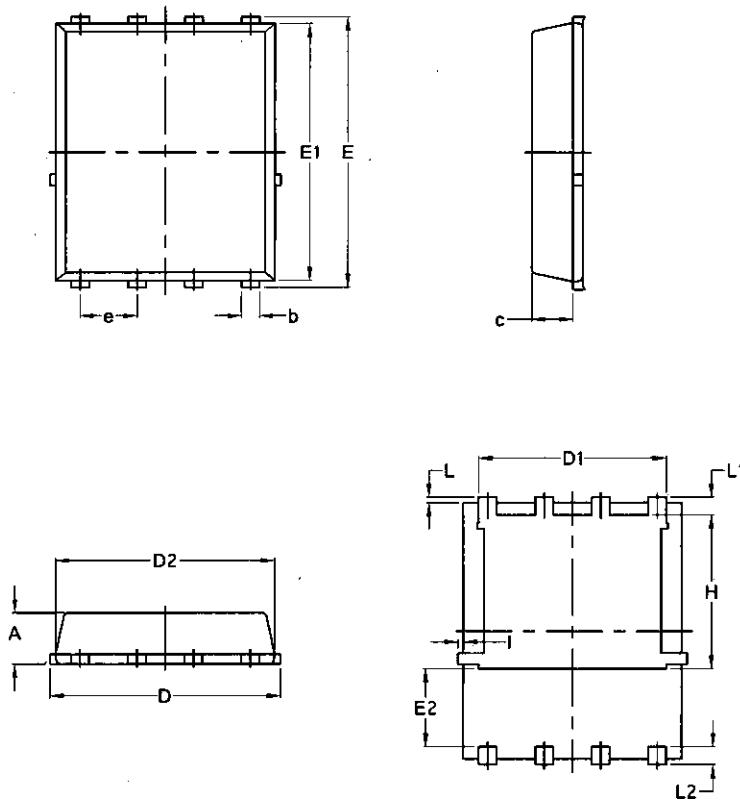


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Package Mechanical Data-PDFN5060-8L- Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070